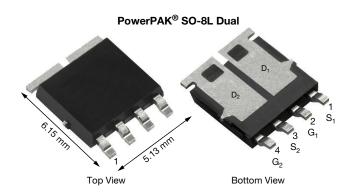


## Automotive Dual N-Channel 100 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY					
V <sub>DS</sub> (V)	100				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0920				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.1170				
I <sub>D</sub> (A) per leg	11				
Configuration	Dual				
Package	PowerPAK SO-8L				

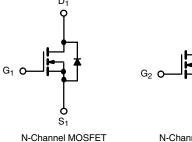
#### **FEATURES**

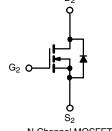
- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % Rq and UIS tested
- · Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





RoHS COMPLIANT HALOGEN **FREE** 





N-Channel M	IOSFET
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<b>ABSOLUTE MAXIMUM RATING</b>	iS (T <sub>C</sub> = 25 °C, unles	s otherwise noted	)		
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-source voltage		V <sub>DS</sub>	100	V	
Gate-source voltage		V <sub>GS</sub>	± 20		
Continuous drain current	T <sub>C</sub> = 25 °C	1	11		
	T <sub>C</sub> = 125 °C	I <sub>D</sub>	6		
Continuous source current (diode conduction	I <sub>S</sub>	15	Α		
Pulsed drain current <sup>b</sup>		I <sub>DM</sub>	17		
Single pulse avalanche current	L = 0.1 mH	I <sub>AS</sub>	9		
Single pulse avalanche energy	ngle pulse avalanche energy		4	mJ	
Maximum power dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	D	27	W	
	T <sub>C</sub> = 125 °C	$P_{D}$	9	VV	
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C	
Soldering recommendations (peak temperature) d, e			260		

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount <sup>c</sup>	$R_{thJA}$	85	°C/W
Junction-to-case (drain)		$R_{thJC}$	5.5	C/VV

#### Notes

- a. Package limited
- b. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %
- c. When mounted on 1" square PCB (FR4 material)
- d. See solder profile (www.vishav.com/doc?73257). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components



PARAMETER	SYMBOL	TES	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-source breakdown voltage	V <sub>DS</sub>	V <sub>GS</sub> =	= 0 V, I <sub>D</sub> = 250 μA	100	-	-	V
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	: V <sub>GS</sub> , I <sub>D</sub> = 250 μA	1.5	2.0	2.5	V
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	0 V, V <sub>GS</sub> = ± 20 V	-	-	± 100	nA
		$V_{GS} = 0 V$	V <sub>DS</sub> = 100 V	-	-	1	
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 100 V, T <sub>J</sub> = 125 °C	-	-	50	μΑ
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 100 V, T <sub>J</sub> = 175 °C	-	-	150	
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 \text{ V}$	6	-	-	Α
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 4 A	-	0.0765	0.0920	
Decision of the second of the	Б	V <sub>GS</sub> = 4.5 V	I <sub>D</sub> = 3 A	1	0.0967	0.1170	0
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 4 A, T <sub>J</sub> = 125 °C	=	-	0.1620	Ω
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 4 A, T <sub>J</sub> = 175 °C	-	-	0.2056	
Forward transconductance b	9 <sub>fs</sub>	$V_{DS}$	= 15 V, I <sub>D</sub> = 4 A	-	8.6	-	S
Dynamic <sup>b</sup>						L	
Input capacitance	C <sub>iss</sub>			-	212	280	
Output capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 25 V, f = 1 MHz	-	118	160	pF
Reverse transfer capacitance	C <sub>rss</sub>	_		-	15	20	-
Total gate charge <sup>c</sup>	Qg			-	4.7	8	
Gate-source charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = 10 V	$V_{DS} = 50 \text{ V}, I_D = 3 \text{ A}$	-	0.8	-	nC
Gate-drain charge <sup>c</sup>	Q <sub>gd</sub>			-	1.3	-	
Gate resistance	R <sub>g</sub>		f = 1 MHz		4	6	Ω
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>			-	9	15	
Rise time <sup>c</sup>	t <sub>r</sub>	V <sub>DD</sub> =	50 V, $R_L$ = 33.3 Ω	-	5	10	
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>		$V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	15	30	ns
Fall time <sup>c</sup>	t <sub>f</sub>		1		5	10	
Source-Drain Diode Ratings and Charact	eristics b	1					
Pulsed current <sup>a</sup>	I <sub>SM</sub>			-	-	17	Α
Forward voltage	V <sub>SD</sub>	I <sub>F</sub> =	= 4 A, V <sub>GS</sub> = 0 V	-	0.88	1.2	V
Body diode reverse recovery time	t <sub>rr</sub>			-	29	60	ns
Body diode reverse recovery charge	Qrr	- I <sub>F</sub> = 3 A, di/dt = 100 A/μs		-	27	55	nC
Reverse recovery fall time	t <sub>a</sub>			19	-	ns	
Reverse recovery rise time	t <sub>b</sub>			-	10	-	ns
Body diode peak reverse recovery current	I <sub>RM(REC)</sub>			-	-1.9	-	Α

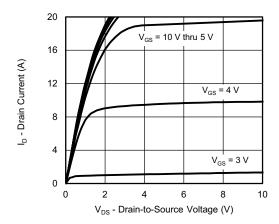
#### Notes

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

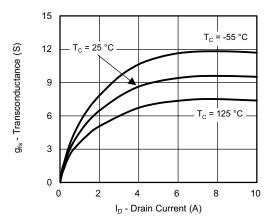
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



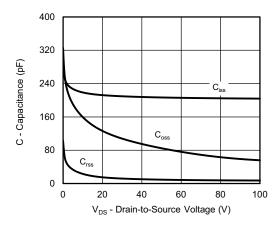
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



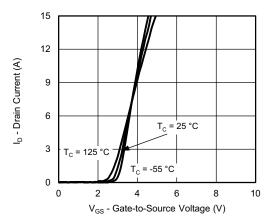
### **Output Characteristics**



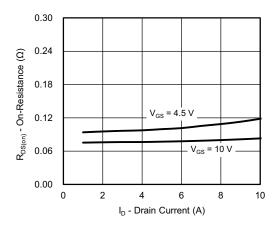
Transconductance



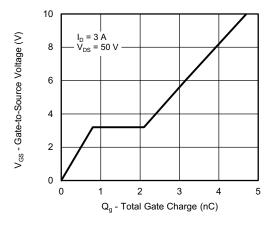
Capacitance



**Transfer Characteristics** 



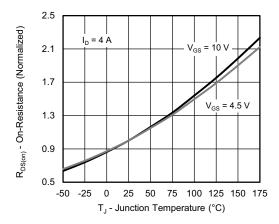
On-Resistance vs. Drain Current



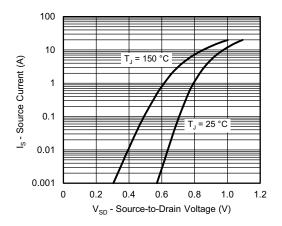
**Gate Charge** 



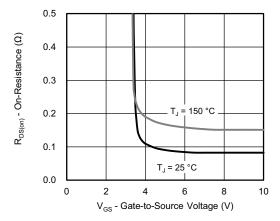
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



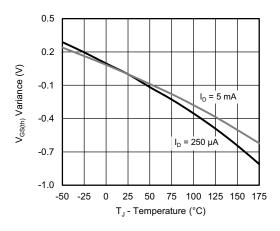
On-Resistance vs. Junction Temperature



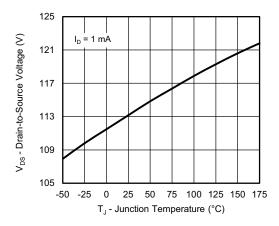
**Source Drain Diode Forward Voltage** 



On-Resistance vs. Gate-to-Source Voltage



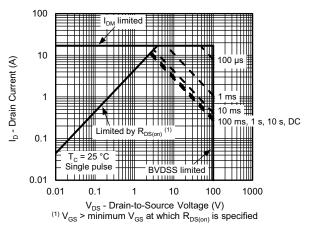
Threshold Voltage



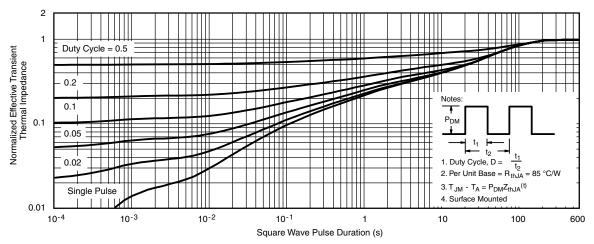
Drain Source Breakdown vs. Junction Temperature



## **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)



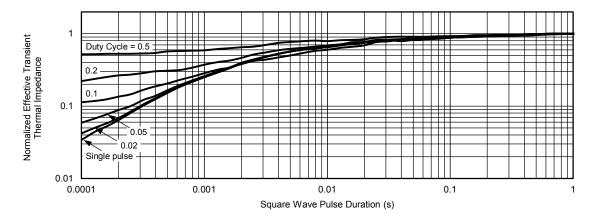
### Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



## THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



#### Normalized Thermal Transient Impedance, Junction-to-Case

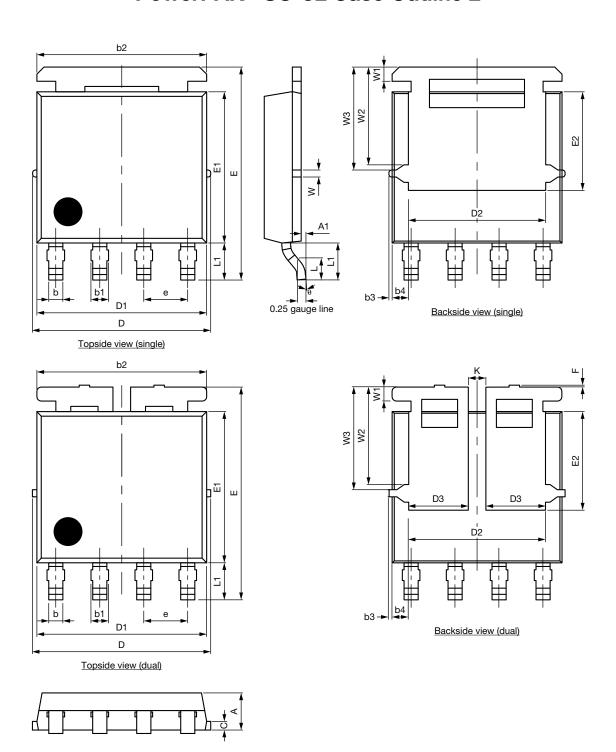
#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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## PowerPAK® SO-8L Case Outline 2



DIM.		MILLIMETERS			INCHES		
DIN.	MIN.	NOM.	MAX. MIN. NOM. N		MIN. NOM.		
А	1.00	1.07	1.14	0.039	0.042	0.045	
A1	0.00	-	0.127	0.00	-	0.005	
b	0.33	0.41	0.48	0.013	0.016	0.019	
b1	0.44	0.51	0.58	0.017	0.020	0.023	
b2	4.80	4.90	5.00	0.189	0.193	0.197	
b3		0.094			0.004	•	
b4		0.47			0.019		
С	0.20	0.25	0.30	0.008	0.010	0.012	
D	5.00	5.13	5.25	0.197	0.202	0.207	
D1	4.80	4.90	5.00	0.189	0.193	0.197	
D2	3.86	3.96	4.06	0.152	0.156	0.160	
D3	1.63	1.73	1.83	0.064	0.068	0.072	
е		1.27 BSC		0.050 BSC			
Е	6.05	6.15	6.25	0.238	0.242	0.246	
E1	4.27	4.37	4.47	0.168	0.172	0.176	
E2	2.75	2.85	2.95	0.108	0.112	0.116	
F	-	-	0.15	-	-	0.006	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
K		0.51			0.020		
W		0.23		0.009			
W1	0.41		0.016				
W2	2.82			0.111			
W3		2.96			0.117		
θ	0°	-	10°	0°	-	10°	

ECN: C21-1498-Rev. C, 01-Nov-2021

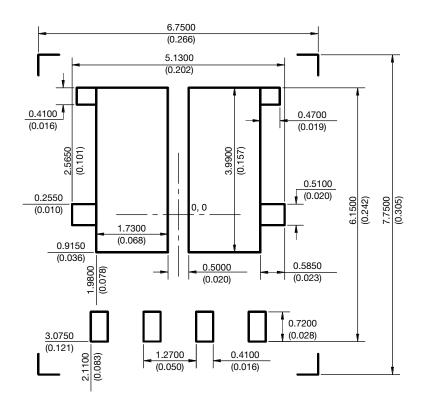
DWG: 6044

### Note

• Millimeters will govern



### RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L DUAL



Recommended Minimum Pads Dimensions in mm (inches) Keep-out 6.75 (0.266) x 7.75 (0.305)



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